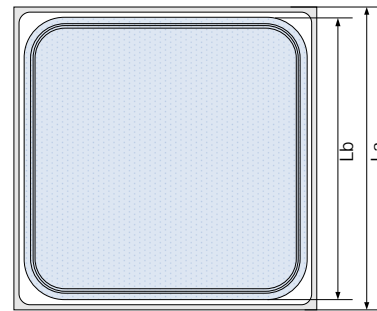


2SB154100MA LOW IR SCHOTTKY BARRIER DIODE CHIPS
DESCRIPTION

- Ø 2SB154100MA is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Ø Due to special schottky barrier structure, the chips have very low reverse leakage current (typical $I_R=0.002\text{mA}@ V_r=100\text{V}$) and maximum 150°C operation junction temperature;
- Ø Low power losses, high efficiency;
- Ø Guard ring construction for transient protection;
- Ø High ESD capability;
- Ø High surge capability;
- Ø Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- Ø Chip Size: $1540\mu\text{m} \times 1540\mu\text{m}$;
- Ø Chip Thickness: $280\pm 20\mu\text{m}$;


Chip Topography and Dimensions

 La: Chip Size: $1540\mu\text{m}$;

 Lb: Pad Size: $1340\mu\text{m}$;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB154100MAYY	For Axial leads package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	100	V
Average Forward Rectified Current	IFAV	3	A
Peak Forward Surge Current@8.3ms	IFSM	80	A
Maximum Operation Junction Temperature	TJ	150	$^\circ\text{C}$
Storage Temperature Range	TSTG	-40~150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{\text{amb}}=25^\circ\text{C}$)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	$I_R=0.5\text{mA}$	100	--	V
Forward Voltage	V _F	$I_F=3\text{A}$	--	0.85	V
Reverse Current	I _R	$V_R=100\text{V}$	--	0.5	mA